Full counting statistics of a chaotic cavity with asym metric leads

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A bstract. We study the statistics of charge transport in a chaotic cavity attached to external reservoirs by two openings of di erent size which transm it non-equal num ber of quantum channels. An exact form ula for the cum ulant generating function has been derived by means of the Keldysh-G reen function technique within the circuit theory of mesoscopic transport. The derived form ula determines the full counting statistics of charge transport, i.e., the probability distribution and all-order cum ulants of current noise. It is found that, for asymmetric cavities, in contrast to other mesoscopic systems, the third-order cum ulant changes the sign at high biases. This e ect is attributed to the skew ness of the distribution of transmission eigenvalues with respect to forward/backward scattering. For a symmetric cavity we nd that the third cum ulant approaches a voltage-independent constant proportional to the tem perature and the number of quantum channels in the leads.

1. Introduction

Statistical properties of charge transfer in m esoscopic conductors have recently received rapidly growing attention. A powerful theoretical approach to the uctuation problem is based on the concept of full counting statistics (FCS) [1]. It gives the probability to transmit a given number of charges from one term inal of a mesoscopic conductor to another term inal during the observation time. From the knowledge of these probabilities one can readily derive not only average current and noise, but all higher cumulants of current uctuations and extrem e-value statistics. Thus FCS represents the complete inform ation which can be gained from charge counting in a transport process.

Since the introduction of FCS for electron counting in mesoscopic conductors by Levitov and co-workers [1], the approach has been successfully applied to various systems including quantum point contacts, di usive conductors, cavities, metal and superconductor junctions [2]. Until very recently, the experimental measurements were focused mainly on shot noise the second cumulant of the uctuating current [3]. Experimental investigation of FCS has been opened up by measurements of the third cumulant of current uctuations [4, 5]. Since the third cumulant (odd-order cumulant) changes sign under a time reversal transformation, it is not masked by thermal uctuations and can be observed at relatively high temperatures [6]. In contrast, accurate measurements of the second cumulant or shot noise (even-order cumulant) is di cult because of the requirement to maintain a low temperature at a high applied voltage.

In this paper we address the FCS of an asymmetric chaotic cavity with two attached leads supporting non-equal number of quantum channels. Previous studies on asymmetric chaotic cavities include the following. The second cumulant has been calculated by Nazarov [7] by means of a circuit theory, by Beenakker [8] using random m atrix theory (RMT), by B lanter and Sukhorukov sem iclassically [9], and by Schanz et al [10] using quantum graphs. The third and fourth cum ulants of current were obtained by Blanter et al [11]. The authors found a discrepancy between sem iclassical and RM T results for high-order cum ulants starting from the fourth cum ulant. Subsequently, Nagaev et al [12] were able to explain the discrepancy by taking into account \cascade correlations" [13] between the cum ulants within a sem iclassical approach. It was pointed out, that evaluation of high-order cum ulants goes beyond the validity of the standard Boltzm ann-Langevin scheme: one has to use cascade diagrams, or to introduce nonlocal noise correlators in the Boltzmann-Langevin equation [14]. It should be noted that the results on the third and forth cumulants of current uctuations [11, 12] were obtained in the zero tem perature lim it only. Experim entalm easurem ents of the second cum ulant (shot-noise) on chaotic cavities were perform ed by Oberholzer et al [15, 16]. Recently, a stochastic path integral approach has been formulated by Pilgram et al [17] and Jordan et al [18], which is e cient to study FCS for arbitrary mesoscopic sem iclassical system s including stochastic networks. The authors [18] have derived the diagram m atic rules to calculate the high-order cum ulants of current uctuations which

take into account the N agaev's cascade correction term s [13]. This approach was applied to calculate the cum ulants of charge uctuations in asymmetric cavities in the regime of strong electron-electron scattering [17, 19]. P ilgram and Buttiker studied the electron scattering on uctuations of charge inside the cavity [20].

In this paper, we use the extended Keldysh-G reen function technique within the circuit theory introduced by Nazarov [21]. By using this technique, we have obtained the cum ulant generating function (CGF) in exact analytical form which contains com plete information about all-order cumulants of current uctuations in asymmetric chaotic cavities at arbitrary bias-to-temperature ratio. The analytical formula for CGF is expressed in terms of the anticom mutator of the matrix G reen functions in the leads. In this form it can be applied to calculate all-order cumulants of current noise and extrem e-value statistics for di erent types of the contacts. In section 2, we present the derivation of CGF for asymmetric cavities and show the correspondence with the results obtained earlier in the symmetric limit. The distribution function of charge transfer is obtained in section 3. The rst three cum ulants of current uctuations are analyzed in section 4 for arbitrary bias-to-tem perature ratio. The third-order cum ulant was found to be linear in voltage at both low and high biases, but, in contrast to other m esoscopic system s, it changes the sign at high biases for any asymmetry of the cavity except the ideally symmetric case. For the symmetric cavity we found a saturation of the third cum ulant with bias at the value proportional to the tem perature and the number of channels in the leads. We explain the change of sign for the third cum ulant as a feature of skew ness of the distribution function of transmission eigenvalues. This is con im ed by the analysis of the tem perature dependent third cumulant for an arbitrary m esoscopic conductor in section 5. In the Appendix we show the correspondence between the CGF obtained in the present paper and the RM T results in the zero tem perature limit.

2. Cum ulant generating function

A chaotic cavity is a conducting island of inegular shape connected to external leads by two quantum point contacts (gure 1). The openings are assumed to be small compared to the size of the cavity. The leads are connected to electron reservoirs kept in local therm al equilibrium with chemical potentials $_{\rm L}$ and $_{\rm R}$. The difference in chemical potentials $_{\rm L}$ $_{\rm R}$ = eV gives rise to a current I owing through the cavity. For simplicity, the quantum point contacts are assumed to be completely transparent, i.e., their widths are adjusted to conductance plateaus [15]. We disregard possible Coulom b blockade e ects, which is justified if the conductances of the leads $G_{\rm L} = G_0 N_{\rm L}$, $G_{\rm R} = G_0 N_{\rm R}$ are assumed to be much larger than the conductance quantum $G_0 = e^2 = h$. This means a multichannel transport regime and negligible weak localization e ects. The inelastic relaxation inside the cavity is disregarded, so the energy of each electron entering the cavity is conserved. Since we are interested only in low-frequency limit of current uctuations, the screening e ects in the cavity are neglected. It is also assumed that the measurement circuit has negligible impedance in order to avoid the environm ental e ects on the statistics of current uctuations [22].

We apply a circuit theory of FCS based on equations for the Keldysh-Green functions [21]. Its main idea is to represent a mesoscopic system by a set of discrete elements: terminals, nodes and connectors. In contrast to conventional classical circuits, in which the nodes are described by a scalar electric potential, here the nodes are characterized by matrix Green functions. The matrix currents owing between the nodes and obeying matrix analogs of Kircho rules contain all current correlators [21, 23, 24, 25, 26].

The circuit theory representation of a chaotic cavity is depicted in gure 1 (right panel). It consists of two term inals (the left and right reservoirs), a central node (the cavity) and two connectors (the left and right point contacts). The term inals and the node are described by 2 2 m atrix G reen functions in K eldysh space: G_L , G_R , and G_c , respectively. The term inalm atrices are assumed to be known and they are given by

$$G_{L} = e^{i_{z}^{2}}G_{L}^{0}e^{i_{z}^{2}}; \quad G_{R} = G_{R}^{0};$$
(2.1)

$$G_{k}^{0} = \frac{1 \ 2f_{k}}{2(1 \ f_{k})} \ 2f_{k} \qquad ; \quad k = L; R; \qquad (2.2)$$

where the counting rotation is applied to the left term inal, $_z$ is the third Paulim atrix and the energy dependent Ferm i function f_k (") = f1 + exp[(" $_k$)= kT_k]g¹ accounts for the electrochem ical potentials $_k$ and the tem peratures T_k in the reservoirs. For a two-term inal conductor, it is su cient to introduce only one counting eld by gauge transform ation in the left term inal. Since we focus only to low-frequency lim it of current uctuations, is taken as a time independent constant.

The matrix current between each connector k and a central node is given by [23]

$$I_{k} = \frac{X}{n} \frac{T_{n}^{k} [G_{k}; G_{c}]}{4 + T_{n}^{k} (fG_{k}; G_{c}g - 2)};$$
(2.3)

Each connector k is characterized by a set of transmission eigenvalues T_n^k associated with n quantum channels at energy ". For fully transparent ballistic point contacts $T_n^k = 1$ for n N_k and $T_n^k = 0$ for n > N_k, that corresponds to having N_L and N_R open channels. In general N_L \in N_R. Thus the matrix current conservation I_L + I_R = 0 gives

$$N_{L} \frac{[G_{L};G_{c}]}{2 + fG_{L};G_{c}g} + N_{R} \frac{[G_{R};G_{c}]}{2 + fG_{R};G_{c}g} = 0:$$
(2.4)

Here, the only unknown function is the matrix G_c , which is isotropic within the cavity under a quantum chaotic regime. Since the term inal matrices G_k and the node matrix G_c are traceless, they can be expanded over the Pauli matrices [25]: $G_k = v_k \sim$, $G_c = v_c \sim$, where v_k and v_c are three-dimensional vectors, and $\sim = (x; y; z)$ is the vector of the Pauli matrices. With the use of this parametrization the anticom mutators $fG_k; G_cg = 2v_k$ of $G_L; G_Rg = 2v_L$ are scalar functions. Introducing the notation $G_L; G_R = v_k \sim 0$

$$p_{k} = \frac{N_{k}}{2 + fG_{k};G_{c}g}; \qquad (2.5)$$

we rewrite equation (2.4) as $[G_{c}] = 0$, from which we obtain $p_{L}v_{L} + p_{R}v_{R} = cv_{c}$, where c is the constant to be found. Using the normalization conditions $v_{k}^{2} = v_{c}^{2} = 1$ and denoting $N_{+} = (N_{L} + N_{R})=2$, we obtain the set of equations

$$c^{2} = p_{L}^{2} + p_{R}^{2} + p_{L}p_{R} fG_{L};G_{R}g;$$
 (2.6)

$$2p_{\rm L} = N_{+} \qquad \alpha N_{\rm R} = N_{+};$$
 (2.7)

$$2p_{R} = N_{+} \quad dN_{L} = N_{+};$$
 (2.8)

from which the constant c can be found explicitly:

$$c = N_{+} (1 + p_{-1})^{1};$$
 (2.9)

$$a = \frac{4N_{\rm L}N_{\rm R}}{(N_{\rm L} + N_{\rm R})^2} \quad 1 \quad \frac{4}{2 + fG_{\rm L};G_{\rm R}g} \quad : \tag{2.10}$$

Our aim is to nd the CGFS () related to the matrix current by [23]

$$\frac{\Theta S}{\Theta} = i \pm \frac{d''}{h} \operatorname{Tr}(_{z} I_{L}); \qquad (2.11)$$

where t is the observation time, which is assumed to be much longer than both the correlation time of current uctuations and the characteristic time e=I with I the time-averaged current. The latter condition ensures that the number of electrons transferred during the time t is much greater than 1. Substituting $I_L = p_L [G_L;G_c]$ and doing matrix transform ations we obtain

$$\frac{\partial S}{\partial t} = t^2 \frac{d''}{h} A; \qquad (2.12)$$

with

$$A = \frac{p_{\rm L} p_{\rm R}}{c} \frac{\theta}{\theta} fG_{\rm L}; G_{\rm R} g:$$
(2.13)

To nd the CGF from equation (2.12) explicitly, we have to integrate A over . To this end all the variables in equation (2.13) can be expressed in term s of the anticom m utator $G = f_{G_L}; G_R g$ by m eans of equations (2.6) { (2.10). We get

$$A = N_{+} \frac{1}{G} \frac{p}{2} \frac{1}{2} \frac{a@G}{@};$$
(2.14)

where the function a() is determined by equation (2.10). Then we use the parametrization a = 4x(1 x), that leads to

$$A = 2N_{+} \frac{(1 \ 2x)}{x [1 \ x (1 \ x)F^{1}]} \frac{0}{2}; \qquad (2.15)$$

where

$$F = \frac{N_{\rm L} N_{\rm R}}{(N_{\rm L} + N_{\rm R})^2}$$
(2.16)

is the constant which will appear below as the Fano factor. Integrating equation (2.12) over by making use of equation (2.15), we obtain the nalformula for the CGF

$$S() = t(N_{L} + N_{R})^{2} \frac{d''}{h_{l}} S_{*}();$$
 (2.17)

$$S_{*}() = L \ln \frac{L}{1 R} + R \ln \frac{R}{1 L};$$
 (2.18)

with

$$x() = [1 + \frac{q}{1 a()}] = 2;$$
 (2.19)

$$_{k} = \frac{N_{k}}{N_{L} + N_{R}}; \quad k = L;R:$$
 (2.20)

It is important that the analytical result for the CGF is expressed through the anticommutator fG_L ; G_R g of arbitrary (traceless) 2 2 m atrix G reen functions at the term inals. Therefore the obtained form ula is valid for di erent types of contacts. y

For norm alm etals with the help of equation (2.2), the anticommutator G reads

$$G = 2 + 4 [f_{L} (1 f_{R}) (e^{i} 1) + f_{R} (1 f_{L}) (e^{i} 1)]:$$
(2.21)

It is worth noticing that our results are in agreement with the RMT theory. As we show in the Appendix, the distribution of transmission eigenvalues (T) obtained from equation (2.17) in the zero temperature limit gives the RMT result. We have also veried the correspondence of our results with the stochastic path integral approach. The saddle-point solutions of the action in [17] can be found not only in the symmetric limit, but quite generally for an arbitrary asymmetric cavity, and we have checked that the result is identical to equation (2.17).

The sem iclassical electron distribution function f_c inside the cavity can be obtained from the matrix G reen function in the central node

$$G_{c} = {}_{L}G_{L} + {}_{R}G_{R} + [x() 1]G_{L} + G_{R}):$$
 (2.22)

In the limit ! 0 we obtain $G_c = {}_{L}G_{L}^{0} + {}_{R}G_{R}^{0}$, which with the help of equation (2.2) gives the distribution function in the cavity $f_c = {}_{L}f_{L} + {}_{R}f_{R}$ derived earlier by other methods [9].

In the symmetric limit N $_{\rm L}$ = N $_{\rm R}$ = N , $_{\rm L}$ = $_{\rm R}$ = 1/2, the CGF in equation (2.17) is simplified to

$$S_{*}^{sym}$$
 () = $\ln [(2 + \frac{p}{2 + G}) = 4];$ (2.23)

which corresponds to the result derived by Belzig [26] with the norm alization S(0) = 0.

It is instructive to compare the symmetric and asymmetric cases in the zero temperature limit. We present the results for the characteristic function $e^{\hat{s}}$:

sym () =
$$\frac{1}{2} + \frac{1}{2}e^{i^2}$$
 ^{2M N}; (2.24)

$$() = {}_{\rm L} + \frac{{}_{\rm L} {}_{\rm R}}{{}_{\rm X}() {}_{\rm R}} {}_{\rm R} + \frac{{}_{\rm L} {}_{\rm R}}{{}_{\rm X}() {}_{\rm L}} {}_{\rm L} (2.25)$$

Here, M eV t= h is the number of attem pts per channel, which is the maxim alnum ber of electrons that can be transferred under the restriction imposed by the exclusion principle for fermions [1]. Equation (2.24) has been obtained by B lanter et al from

y A fler submission of the rst version of this paper to the e-archive P reprint cond-m at/0403388], Vanevic and Belzig have proved [27] that formula (2.17) for the CGF is independent of the matrix structure and, in particular, it is valid for 4 4 matrices in Keldysh-Nambu space for superconductor contacts.

the RM T theory [11] and by P ilgram et al by the stochastic path integral method [20]. Equation (2.25) is an extension to the case of cavities with non-equivalent leads, in which the relative numbers of channels $_{\rm k}$ are dened by equation (2.20). The particular form of () can be attributed to interplay of binom ial statistics of the two point contacts in series (cavity openings) with inter-channel mixing inside the cavity. Therefore the logarithm ic functions in equations (2.17) and (2.23) come from the binom ial statistics of two quantum point contacts [1]. The function x in equations (2.17) and (2.25) and the square root in equation (2.23) account for the inter-channel mixing inside the cavity [26].

It is interesting to analyze formula (2.17) in the strongly asymmetric limit when one opening supports many more channels than the other. Let us suppose N_R < N_L. Denoting the parameter of asymmetry = N_R=N_L 1, and expanding the CGF in series of , we get

$$S_{*}() = (\ln) + (^{1} \ 1 \ \ln)^{2} + O(^{3}); \qquad (2.26)$$
$$() = [2 + G()] = 4:$$

In the zero tem perature lim it ! ė, this sim pli es to

$$S_{*}() = i + (e^{i} - 1 - i)^{2} + O(^{3});$$
 (2.27)

We observe that the leading-order term is linear in . This means that the charge transport in the leading-order is just the stationary current with no noise. The current is determined by the opening with the smallest number of channels I $G_0 V N_R$. It does not mean, however, that there are no current uctuations at all. The second cumulant (noise power) and all higher cumulants are determined by the next order term (eⁱ 1)², which depends on both openings. For the noise power, for instance, we obtain P_I 2eI ($N_R = N_L$). At nite temperatures the leading-order term a ects all the cumulants of current uctuations [see equation (2.26)].

3. Electron counting statistics

Having found the CGF S (), we obtain a complete information about the transfer of charges with time through a chaotic cavity. The full counting statistics is determined by the distribution function P (Q) giving the probability of transferring Q charges through a cavity during the observation time t. The distribution function is related to the CGF by Fourier transform:

$$P(Q) = \frac{d}{2} e^{iQ + S()} :$$
 (3.1)

This integral can be evaluated in the stationary phase approximation. In the low-tem perature limit the stationary point is determined by

$$(N_{\rm L} + N_{\rm R}) M \frac{(0.5)}{(0.5)} = iQ : \qquad (3.2)$$

The large number of channels $N_{L,R}$ 1 and long observation time M 1 provide a necessary condition for the observation of a large number of transmitted particles and accurate estimate of the integral in the stationary point. By using the CGF (2.18) we arrive at the pure in aginary value for the stationary point

$$s = i \ln \frac{M N_L}{Q} \quad 1 \quad \frac{M N_R}{Q} \quad 1 \quad (3.3)$$

The maximal number of electrons that can be transferred through each contact separately is given by the product M N_k (the number of attem pts per channelm ultiplied by the number of channels) with k = L; R. Therefore the charge Q transmitted through a cavity is restricted by the limits: $0 < Q < Q_{max}$, where Q_{max} M N_R and N_R is the number of channels in the narrowest contact. We notice that in this interval of allowed values of Q the expression in the logarithm (3.3) is strictly positive and the stationary point does exist. Evaluation of the integral (3.1) in the stationary point (3.3) leads to the result

$$\ln P(Q) = 2Q \ln Q \qquad X \qquad (Q_k Q) \ln (Q_k Q); \qquad (3.4)$$

where Q_k M N_k, k = L;R. It is interesting to see that the probability function is factorized into separate contributions for each contact: $\ln P(Q) = \int_{k=L,R}^{P} L_k$ with $L_k = Q \ln Q (Q_k Q) \ln (Q_k Q).$

The result of the evaluation of ln P (Q) using Eq. (3.4) is shown in Fig. 2 for di erent asymmetries of the cavity $= N_R = N_L$. For a symmetric cavity (=1) the distribution function is symmetric around the average value $Q = Q_{max} = 0.5$ and it is in agreement with the known result: $\ln P_{sym}$ (Q)=Q_{m ax} = $2 [\ln 2 + Q \ln Q + (1 Q) \ln (1 Q)]$ with $Q = Q_{max}$ (see, e.g., Ref. [28]). When is decreased from 1 to 1=100 the cavity Q becomes more and more asymmetric, the maximum P (Q) is shifted from 0.5 to 1 (see Fig. 2). This evolution correponds to the widening of one of the contacts, while the other (the narrowest one) is kept xed. In the strongly asymmetric limit when one opening supports m any m ore channels than the other (1), the distribution function becomes highly asymmetric with a long tail at Q < Q and a sharp drop to zero at Q > Q. The maximum of P (Q) approaches the largest value Q ! Q_{max} determined by the smallest opening. This is in agreement with the fact that the conductance of the cavity (the rst-order cumulant) in this lim it depends only on the smallest opening. The width of P (Q) determines the second cumulant (the noise power). In the strongly asymmetric lim it the second cum ulant and all higher cum ulants are determ ined by the tail of P (Q)at Q < Q described asymptotically as $\ln P(Q)$ (Q_{m ax} Q) $\ln (N_R = N_L)$ and therefore they depend on both openings. This clearly shows the non-Gaussian character of the uctuations of the transmitted charge in asymmetric cavities.

Full counting statistics of a chaotic cavity

4. C um ulants

The cumulants are found from the CGF by di erentiating over the counting eld :

$$C_{k} = \frac{0}{i0} \int_{0}^{1} S() j_{=0}:$$
 (4.1)

The rst few cumulants characterize the features of the distribution P(Q): the rst cumulant gives the mean, the second, the dispersion, and the third, the skewness of the distribution [6].

4.1. M ean current and noise

A lthough the rst two cumulants for the chaotic cavity are already known, it is instructive to see how they emerge in our approach in order to compare with higher cumulants. The rst two cumulants of current uctuations determ ine the mean current and noise:

$$I = \frac{e}{t}C_{1}; \qquad P_{I} = \frac{2e^{2}}{t}C_{2}; \qquad (4.2)$$

From equations (2.17) and (4.1) we obtain

$$I = e \frac{N_{L} N_{R}}{N_{L} + N_{R}}^{2} \frac{d''}{h} (f_{L} - f_{R});$$
(4.3)

$$P_{I} = 2e^{2} \frac{N_{L}N_{R}}{N_{L} + N_{R}}^{2} \frac{d''}{h} f_{L} (1 f_{L}) + f_{R} (1 f_{R}) + \frac{N_{L}N_{R}}{(N_{L} + N_{R})^{2}} (f_{L} f_{R})^{2} : (4.4)$$

For further calculations we assume the same tem perature for all the system, $T_L = T_R = T$, and max(kT;eV) $_k$, k = L; R. We get

$$I = GV; \tag{4.5}$$

$$P_{I} = 4kTG [1 + F (u \coth u \ 1)];$$
 (4.6)

where $G = G_L G_R = (G_L + G_R)$ is the conductance of the cavity, u = V = (2kT), and F is the Fano factor given by equation (2.16). Equation (4.6) has also been obtained sem iclassically [9, 15]. It is seen that the current I is linear in bias for arbitrary tem perature and therefore contains little inform ation about the transport. In contrast, the behavior of the noise power di ers in the two lim its:

$$P_{I} = \begin{pmatrix} 4kTG [1 + (F=12) (eV=kT)^{2}]; eV & kT \\ 2eG VF; & eV & kT: \end{cases}$$
(4.7)

At low biases (high temperatures) the second cumulant, as an even-order cumulant, is dominated by thermal noise 4kTG. To extract information additional to that obtained from the mean current, one should go to the shot-noise regime eV kT. The measurement of the shot-noise suppression factor $P_I=2qI = F$, gives in principle information about the cavity openings. In these measurements a natural diculty is the requirement to maintain the sample coolunder high currents, and to unambiguously interpret the linear dependence of P_I over I as a shot noise and not as a thermal noise modiled by nonlinear conductance [6]. In contrast, the third cumulant is free from this diculty as will be shown in the next section.

4.2. Third-order cum ulant

For the third cum ulant of current uctuations

$$C_{I} = \frac{e^{3}}{t} C_{3};$$
 (4.8)

from equation (2.17) we nd

$$C_{I} = e^{3} \frac{N_{L} N_{R}}{N_{L} + N_{R}}^{2} \frac{d''}{h} (f_{L} f_{R}) f_{1} 3_{1} (f_{L} f_{R})$$

+ $f_{R} (1 f_{L}) + 2_{2} (f_{L} f_{R})^{2};$ (4.9)

where $_1 = 1$ F and $_2 = 1$ $2F + 2F^2$. Integrating over energy, we get

$$C_{I} = ekTG$$
 6F (1 2F) $both u + u = \frac{2(1 F)}{3(1 2F)}$ coth u'' ; (4.10)

which is valid for arbitrary ratio u = eV=2kT between the bias and temperature. A symptotically,

$$C_{I} = \begin{pmatrix} e^{2} IF; & eV & kT \\ eG F [6(1 & 2F) kT & (1 & 4F) eV]; & eV & kT: \end{pmatrix}$$
(4.11)

In the zero tem perature lim it equation (4.11) is in agreem ent with the results in [11, 12]:

$$C_{I}(kT ! 0) = e^{2}IF(1 4F) = e^{2}I\frac{N_{L}N_{R}(N_{L} N_{R})^{2}}{(N_{L} + N_{R})^{4}}$$
: (4.12)

At high temperatures we observe that close to equilibrium C_{I} is linear in bias and independent of temperature, and hence not masked by the Johnson-Nyquist noise. Furtherm ore, it is proportional to the Fano factor F and therefore the measurements of $C_{I}=e^{2}I$ at arbitrarily smallbiases, give directly the factor F with no need to subtract the therm all noise, in contrast to the case of the second cumulant [compare with equations (4.7)]. Another important feature is the change of sign of the third cumulant at high biases. This behavior is illustrated in gure 3 where the third cumulant is shown as a function of bias-to-tem perature ratio for di erent asymmetries of the cavity = $N_{R}=N_{L}$. [is obviously related to the Fano factor, $F = = (1 + \frac{3}{2})$. For the symmetric case (=1), C_{I} approaches the bias-independent constant

$$C_{I}^{\text{sym}}$$
 (eV kT) = $\frac{3}{4}$ eG kT = $\frac{3}{8}$ eG₀kTN (4.13)

proportional to the temperature T and the number of channels N and otherwise independent of the parameters of the material. For asymmetric cavities (0 < < 1), the curves change the sign at eV =kT = $6(1 \quad 2F)=(1 \quad 4F)$ which approaches 6 as ! 0. Equations (4.7) and (4.11) also demonstrate that with the increase of temperature under xed bias the third cumulant saturates, while the second cumulant diverges with T.

Next we focus on the voltage dependence of the third cum ulant for the asymmetric cavity (see gure 4). At low and high biases, C_{I} is approximately linear, with positive and negative slopes, respectively. These linear dependences can easily be deduced from equation (4.11). Note that the slopes, as well as the intersections with the axes, can be used in the experiment to determ ine the parameters of the cavity (the num ber of channels

in each opening). There is a striking similarity of our results with the behavior of C_{I} for a tunnel junction in the electrom agnetic environment modelled by two conductors in series [22]. For the latter, the temperature dependence and the sign change are caused by feedback from the electrom agnetic environment. In the case of a cavity, the sign change is solely due to internal dynamics. This similarity is probably related to the fact that the cavity can also be represented by two conductors (point contacts) in series with interm ode mixing in the node.

A n in portant point is whether the tem perature-dependent third cum ulant obtained from the circuit theory [equation (4.9)] can also be obtained within the sem iclassical Boltzm ann-Langevin picture. The analysis of equations in the work by N agaev et al [12] shows that the same form ula for C_{I} can only be obtained if one takes into account the \cascade corrections". [The authors present the results for C_{I} at zero tem perature only.] At zero tem perature these corrections are only signi cant for cum ulants starting from the forth cum ulant, but at nite tem perature they are essential for the third cum ulant too. This means that the third cum ulant we have obtained from the circuit theory cannot be obtained from the standard Boltzm ann-Langevin scheme; one has to add the cascade correlations between the cum ulants [12, 13]. In addition, it can be shown that the bias independent saturation value of C_{I} for a symmetric cavity [equation (4.13)] originates completely from the \cascade correction" term. The contribution of the m inim alcorrelation term to this value is zero. Thus the experimental measurem ents of the saturation value of the third cum ulant would give the evidence of the cascade correlations in chaotic cavities and the non-locality of the noise correlators.

5. Third-order cum ulant for an arbitrary m esoscopic conductor

Having found the change of sign in the third-order cumulant for chaotic cavities, it is interesting to ask: (i) is this behavior typical, and (ii) what are the necessary conditions to observe the same phenomenon in other types of mesoscopic conductors? Here we focus on the elects caused only by internal dynamics due to elastic scattering; the environmental elects are neglected.

To answer these questions, we consider an arbitrary two-term inal mesoscopic conductor characterized by the distribution of transm ission eigenvalues (T). The CGF for this case can be found with the help of the form ula obtained by Levitov et al [1]. By expanding S () [equation (A 1) in the Appendix] in Taylor series up to O (3), we obtain the third cumulant in the form z

$$C_{I} = eG \overset{Z}{d} (f_{L} \quad f_{R})^{n} \quad 3_{1} [f_{L} (1 \quad f_{R}) + f_{R} (1 \quad f_{L})] + 2_{2} (f_{L} \quad f_{R})^{2}; \quad (5.1)$$
where $G = G_{0} \overset{R_{1}}{_{0}} (T) T dT$ is the Landauer conductance and the other constants are
$$\overset{Z}{_{1}}_{1} = \overset{Z}{_{0}} (T) T^{2} dT; \quad 2 = \overset{Z_{1}}{_{0}} (T) T^{3} dT; \quad (5.2)$$

z The rst and the second cumulant of current uctuations for arbitrary conductor are given by equations (4.5) and (4.6), respectively, in which G and F are determined by (T).

with $G_0=G$. Integrating over energy under the assumption max(kT;eV) $_k$, k = L;R, we obtain

$$C_{I} = ekTG [cothu + u(1 cothu)] + 2F_{3}u$$
 (5.3)

as a function of the bias-to-tem perature ratio u = eV=(2kT). A sym ptotically,

$$C_{I} = \begin{pmatrix} e^{2}IF; & eV & kT \\ eG [(kT + F_{3}eV]; eV & kT; \end{pmatrix}$$
(5.4)

where

$$F = 1 \qquad _{1} = \qquad _{0} T (1 T) dT;$$

= 6(12) = 6 T²(1 T) dT;
$$F_{3} = 1 \qquad _{1} + 2 = \qquad _{0} T (1 T) (1 2T) dT;$$
(5.5)

It is seen that at low biases the third-order cum ulant is given by the universal relation $C_I = e^2 IF$ for any distribution of transm ission eigenvalues (T). This means that, at low biases, C_I for any conductor is: (i) independent of tem perature, (ii) linear in voltage with a positive slope, and (iii) proportional to the Fano factor F. At high biases, the voltage dependence of C_I is also linear, with the slope determ ined by the constant F_3 . The slopes in the low-bias and high-bias regimes are dimensioned in the unique case of a tunnel junction, for which all the tunneling probabilities are small, T 1, and F F_3 1, 0. The latter is in agreement with the prediction by Levitov and Reznikov [6].

The slope of C_{I} can be negative, that means C_{I} (V) changes sign, if and only if $F_{3} < 0$. Let us focus our analysis on the sign of the constant F_{3} . We observe that the function (T) T (1 T)(1 2T) obeys (1 T) = (T). Hence we can write

$$F_{3} = \begin{bmatrix} Z_{1=2} \\ [(T) (1 T)] (T) dT; \qquad (5.6)$$

where the range of integration is reduced to 0 < T < 1=2. It is clear that the sign of this integral depends on the function in the square brackets only, since (T) > 0. Denoting (T) (T) (1 T), we observe that (T) is related to the asymmetry or skewness of the distribution (T) around the midpoint T = 1/2. If the backscattering dom inates, we can expect (T) > 0 and $F_3 > 0$. If the forward transmission dom inates, one can expect (T) < 0 and $F_3 < 0$. Thise ect ismuch better pronounced in the case of a one-channel conductor [6], for which (T) = (T T) and the sign of F_3 depends on the condition whether T_1 is greater or smaller than 1/2.

In principle, one can calculate the coe cient F₃ for any mesoscopic conductor, for which the distribution (T) is known (for di erent types of the distributions see, e.g., the reviews [3, 8]). We just remark that for di usive metals the distribution function is bim odal (T) $1=(T \ 1 \ T)$ with clear asymmetry in favor of backscattering. One can verify that > 0 and therefore C_I does not change sign. Indeed, direct calculation from equations (5.2) and (5.5) gives, for di usive metals, 1=2/3, 2=8/15,

F = 1/3, = 4/5, $F_3 = 1/15$. This is in agreement with the studies by Nagaev [13] (sem iclassical approach) and G utm an and G effen [29] (nonlinear -m odel), who obtained the tem perature dependent third cum ulant for this case.

For a double-barrier tunnel junction the distribution of eigenvalues is also bim odal: (T) $1 = T^3 (T_{m ax} T)$ with $T_{m in} < T < T_{m ax}$ [30]. A gain, as in the case of di usive m etals, there is a skewness of (T) in favor of backscattering because of two reasons: the shape of the distribution and the gap at high transm issions close to $T_{m ax}$ (the gap at sm all transm issions is much sm aller [30]). The coe cients for this case can be found: $_1 = 1$ F, $_2 = (3=2)(1$ F)², = 3(1 F)(1 3F), F = 1 3F + 3F², where the Fano factor F = $(g_L^2 + g_R^2) = (g_L + g_R)^2$ is determ ined by the conductances g_L and g_R of the barriers. The coe cient F $_3$ in the zero-tem perature limit for this case has been derived by de Jong [30]. It is seen that $F_3 > 0$ for any F, including the case of a symmetric junction for which the Fano factor takes its maxim alvalue F = 1/2. Therefore C_I for double-barrier tunnel junctions is always positive.

For chaotic cavities, the function (T) is bim odal again (see equation (A.4) in the Appendix]; however, in contrast to the previous cases, it is asymmetric in favor of the forward scattering due to a gap at low transmissions $0 < T < T_c$. Therefore for asymmetric cavities < 0. The gap disappears only when the cavity is ideally symmetric. In this case 1= T (1 T) and = 0. Indeed, from equation (T) 0, which is equal to zero only when F = 1/4(4.11) follows that $F_3 =$ (1 4F) for a symmetric cavity. Therefore the negative slope of the voltage-dependent third cum ulant in asymmetric chaotic cavities is caused by the skewness in the transmissions when forward scattering prevails over backward scattering. The voltage independent asymptotics occurs only when the function (T) is symmetric with respect to the m idpoint T = 1/2.

Sum marizing these examples, we conclude that the third-order cum ulant of current uctuations is an important quantity characterizing the asymmetry of the distribution of transmission eigenvalues (T) with respect to forward and backward scattering. While the average value is described by the conductance G, and the \bim odality" (dispersion) is determined by the Fano factor F, the skewness is captured by the factor F_3 , in particular by its sign. Therefore, the measurements of the third-order cum ulant would give information additional to that obtained from the rst-and the second-order cum ulants.

6. Sum m ary

By using the extended Keldysh-Green function technique of the circuit theory, we have derived the analytical formula for the cumulant generating function of current uctuations in a chaotic cavity with asymmetric leads at an arbitrary bias-to-tem perature ratio. The CGF contains a complete information about all-order cumulants, and it is expressed in term softhe anticommutator of the matrix Green functions at the leads, and therefore can be applied to di erent types of the contacts (see footnotey).

We emphasize the importance of know ledge of the CGF for any stochastic problem : it gives not only the cumulant of any order, but also the probability distribution of a certain event including \rare" events (extrem e-value statistics), which cannot be obtained from the know ledge of the rst few cumulants.

Form etalcontacts with Ferm i-D irac lling factors and fully transparent leads, going beyond the previous studies at zero tem perature, we have found that the third cum ulant of current noise C_I changes sign at high biases for any asymmetric cavity except in the case when the number of quantum channels in the two leads are equal (symmetric cavity). This e ect is attributed to the skewness of the distribution of transmission eigenvalues with respect to forward/backward scattering. For the asymmetric case, C_I is linear in bias at both low and high voltages with positive and negative slopes, respectively. For the symmetric cavity, C_{T} is linear at low voltages and it is constant at high voltages with the value proportional to the tem perature and the num ber of quantum channels. This value was found to be related to the cascade correlations between the cum ulants. At low biases (or, equivalently, at high tem peratures), the third cum ulant is proportional to the Fano factor F and independent of tem perature. This fact can be used in the experiment to measure the Fano factor F from the ratio $C_{I}=e^{2}I$ at arbitrarily sm all biases. In contrast to the case of tunnel junctions, for which C_I m ay change sign due to e ect of the environm ent, in asymmetric cavities C I changes sign due to internal dynamics. The correspondence with other theories: the RMT theory, the cascaded Langevin approach, and the stochastic path integralm ethod has been discussed.

The rst successful measurements of the third cum ulant in tunnel junctions [4, 5] leads us to believe that sim ilar measurements can be performed for cavities and other mesoscopic systems.

Appendix A.Correspondence with RMT

Levitov's form ula for the CGF provides a connection between the FCS and the scattering properties of a two-term inalm esoscopic conductor [1]:

$$S() = t \frac{d''}{h_0} \frac{d''}{0} (T) \ln f 1 + T [G() 2] = 4g dT;$$
 (A.1)

where (T) is the distribution of transm ission eigenvalues. In the zero-tem perature lim it this form ula can be inverted to nd the function (T) from the CGFS() by analytical continuation in the complex plane [28]

$$(T) = \frac{1}{T^2} \operatorname{Im} \overset{0}{\overset{0}{e}} \frac{@S_{*}}{@} \overset{1}{\underset{! = T i0^{+}}{}^{A}} :$$
 (A.2)

where e^{i} 1. One can nd (T) for an asymmetric cavity by substituting Eq. (2.18) into (A 2). The shortest way, however, is to use directly the derivative from (2.14), one obtains

$$\frac{@S_{"}}{@} = \frac{1}{G()} \frac{q}{2} \frac{1}{@} \frac{a()}{@} \frac{@G}{@} = \frac{1}{2} \frac{0}{@} 1 \qquad S \frac{1}{1 + T_{c}} \frac{1}{A};$$
(A.3)

where $T_c = 1$ 4 $_L$ $_R = (N_L N_R)^2 = (N_L + N_R)^2$. Now applying equation (A.2) to (A.3), we arrive at:

$$(T) = \frac{1}{T} \frac{T}{1} \frac{T_c}{1} \frac{T_c}{T_c}; \quad T_c < T < 1; \quad (A.4)$$

and $(T) = 0 \text{ at } 0 < T < T_c$. This coincides with the distribution obtained by Beenakker [8] from the random matrix theory based upon the circular unitary ensemble of chaotic cavities.

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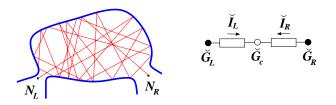
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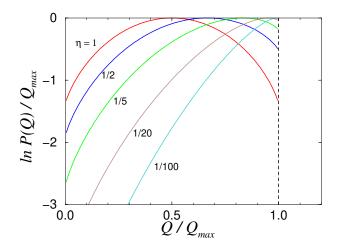
Full counting statistics of a chaotic cavity

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Figure captions



F igure 1. Chaotic cavity with two asymmetric leads supporting N $_{\rm L}$ and N $_{\rm R}$ quantum channels (left) and its circuit theory representation (right) with matrix G reen functions G $_{\rm L}$, G $_{\rm C}$, and G $_{\rm R}$ assigned to each term inal and to a central node. The matrix currents I $_{\rm L}$ and I $_{\rm R}$ obey a K ircho law in a central node.



F igure 2. Counting statistics of charge Q transmitted trough an asymmetric cavity for several parameters of the asymmetry = $N_R = N_L$. The narrowest contact R is kept xed, while the contact L is widened. The charge is normalized to its maximum value $Q_{m ax} = (e^2 V t = h)N_R$ determined by the conductance of the narrowest opening R, and the probability is normalized according to P (Q) = 1 at the point of the average transmitted charge Q = $Q_L Q_R = (Q_L + Q_R)$.

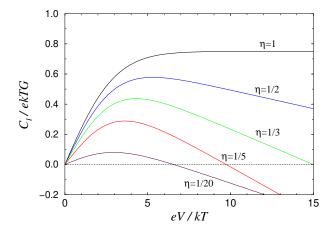


Figure 3. Third cumulant of current uctuations C_{I} as a function of bias-totem perature ratio for di erent degrees of the cavity asymmetry = $N_{R} = N_{L}$. With increasing bias, C_{I} changes sign for any except = 1 for the ideally symmetric case, for which it saturates. For negative biases C_{I} (V) = C_{I} (V).

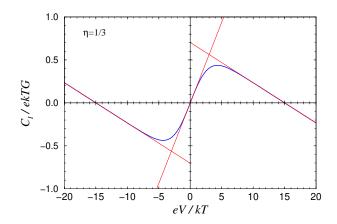


Figure 4. Voltage dependence of the third cumulant C_{I} (blue) for the asymmetric cavity with = 1=3. At low and high biases C_{I} is approximately linear (red) with positive and negative slopes, respectively.